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(54) **BYPASS DIODE FOR A SOLAR CELL**

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USPC **438/59**; 438/66; 438/73; 438/98; 438/751; 257/E27.123; 257/E27.133; 257/E31.038

(58) **Field of Classification Search**
USPC 438/59–66, 73, 98, 751; 257/E27.123, 257/133, 31.038
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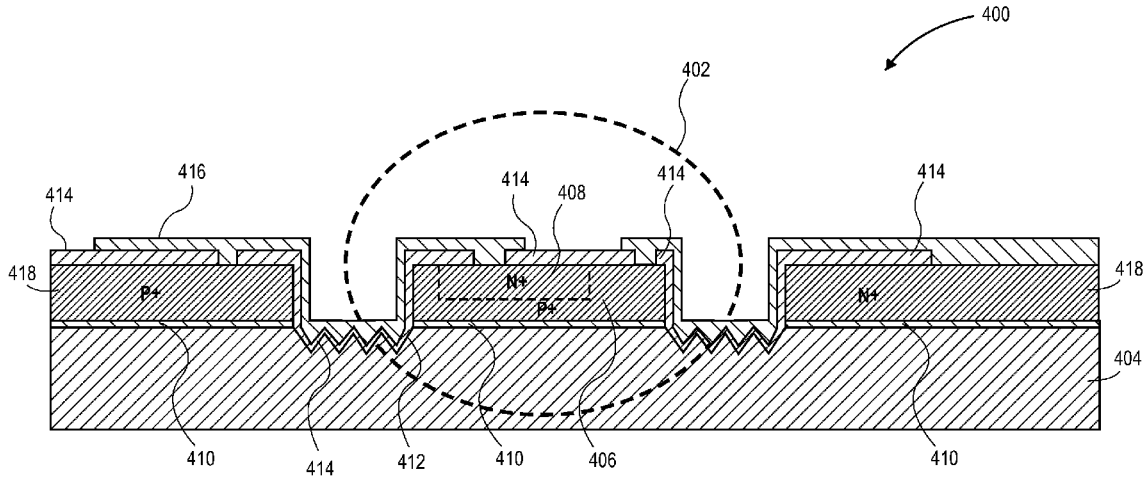
(57) **ABSTRACT**

Methods of fabricating bypass diodes for solar cells are described. In one embodiment, a method includes forming a first conductive region of a first conductivity type above a substrate of a solar cell. A second conductive region of a second conductivity type is formed on the first conductive region. In another embodiment, a method includes forming a first conductive region of a first conductivity type above a substrate of a solar cell. A second conductive region of a second conductivity type is formed within, and surrounded by, an uppermost portion of the first conductive region but is not formed in a lowermost portion of the first conductive region.

24 Claims, 10 Drawing Sheets